

isc Silicon PNP Darlington Power Transistor

2SB1404

DESCRIPTION

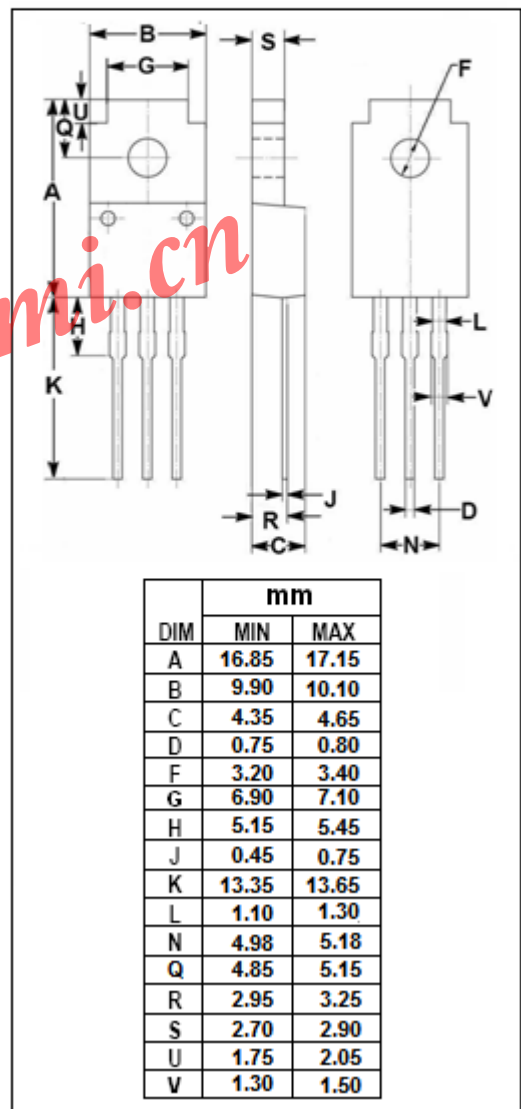
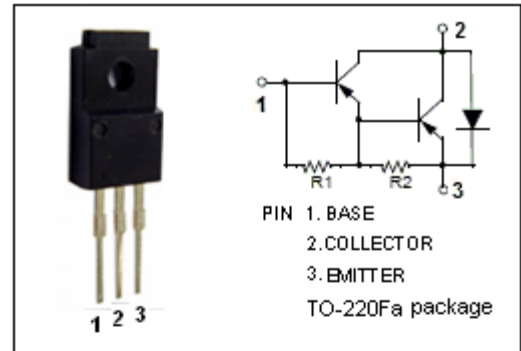
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -120V(\text{Min})$
- High DC Current Gain-
: $h_{FE} = 1000(\text{Min}) @ (V_{CE} = -3V, I_C = -1.5A)$

APPLICATIONS

- Designed for low frequency power amplifier applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-120	V
V_{CEO}	Collector-Emitter Voltage	-120	V
V_{EBO}	Emitter-Base Voltage	-7	V
I_C	Collector Current-Continuous	-3	A
I_{CM}	Collector Current-Peak	-6	A
P_C	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	2	W
	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	25	
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~150	$^\circ\text{C}$



isc Silicon PNP Darlington Power Transistor**2SB1404****ELECTRICAL CHARACTERISTICS****T_j=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -25mA; R _{BE} = ∞	-120			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = -0.1mA; I _E = 0	-120			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = -50mA; I _C = 0	-7			V
V _{CE(sat)-1}	Collector-Emitter Saturation Voltage	I _C = -1.5A; I _B = -3mA			-1.5	V
V _{CE(sat)-2}	Collector-Emitter Saturation Voltage	I _C = -3A; I _B = -30mA			-3.0	V
V _{BE(sat)-1}	Base-Emitter Saturation Voltage	I _C = -1.5A; I _B = -3mA			-2.0	V
V _{BE(sat)-2}	Base-Emitter Saturation Voltage	I _C = -3A; I _B = -30mA			-3.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -100V; I _E = 0			-10	μ A
I _{CEO}	Collector Cutoff Current	V _{CE} = -100V; R _{BE} = ∞			-10	μ A
h _{FE}	DC Current Gain	I _C = -1.5A; V _{CE} = -3V	1000		20000	